

FORM PTO-1449		U.S. Department of Commerce Patent and Trademark Office		Atty. Docket No. BUR920030177US1		Application No. 10/707,905							
<div>NOV 29 2005</div> <div>INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Use several sheets if necessary)</div>				Applicant Douglas D. COOLBAUGH, et al.									
				Filing Date January 23, 2004		Group 2811							
U.S. PATENT DOCUMENTS													
EXAMINER INITIAL		DOCUMENT NUMBER			DATE	NAME	CLASS	SUBCLASS	FILING DATE IF APPROPRIATE				
SPC		6	5	2	1	5	0	6	02/18/03	COOLBAUGH et al.			
		6	0	1	4	0	6	4	01/11/00	BOLES et al.			
		4	5	9	0	4	3	9	05/20/86	GOGGIN			
		3	6	3	8	3	0	0	02/01/72	FOXHALL et al.			
		4	6	4	2	5	8	0	02/10/87	SCOTT			
		4	6	6	8	3	0	6	05/26/87	NISHIZAWA			
		6	5	5	9	0	2	4	05/06/03	BOLES et al.			
	6	5	2	1	9	3	9	02/18/03	YEO et al.				
FOREIGN PATENT DOCUMENTS													
		DOCUMENT NUMBER			DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION YES NO				
SPB	63	-	3	0	0	5	7	0	12/07/88	JAPAN			Abstract
SPC	64	-		1	9	7	7	9	01/23/89	JAPAN			X
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, Etc.)													
SPC	1	An Article of VELLANKI et al., entitled: "Highly Conductive n+ Layers in InP:Fe Created by MeV Energy Si, S, and Si/S Implantation for Application to Microwave Devices", Journal of Electronic Materials, Vol. 22, No. 1, 1993, pp. 73-80											
EXAMINER <i>[Signature]</i> DATE CONSIDERED <i>2/4/06</i>													
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